

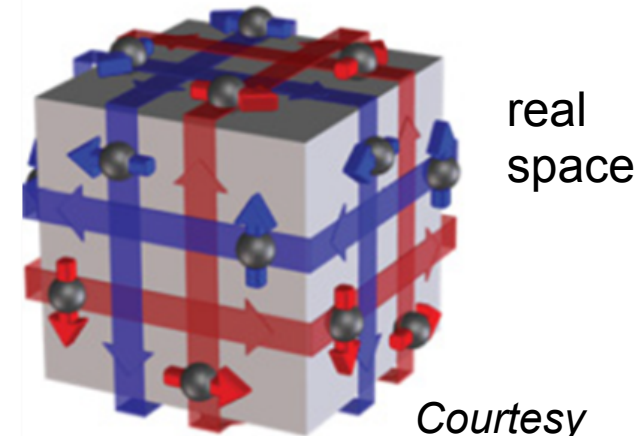
Ultrafast study of Dirac fermions in out of equilibrium Topological Insulators

Marino Marsi

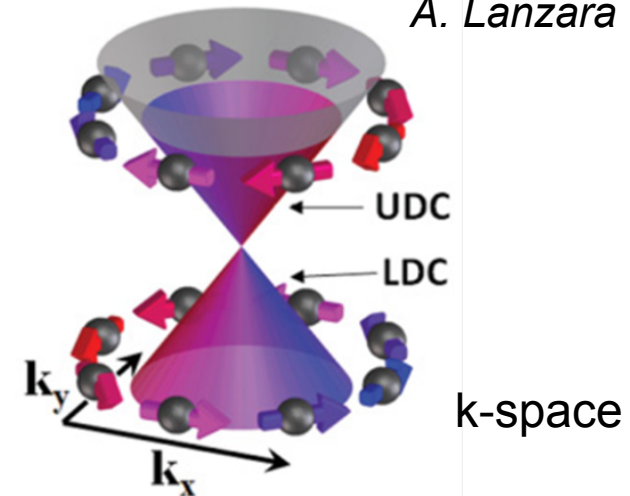
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Topological Insulators

- Novel state of quantum matter
- Insulating bulk, but gapless edge or surface states
- Combined action of spin-orbit coupling and time reversal symmetry (QSH effect)
- Unique transport properties: topologically protected states, immune to defects, perturbation
- Spin locking: the spin of the surface state lies in the surface plane and is always perpendicular to the momentum



Courtesy
A. Lanzara et al.

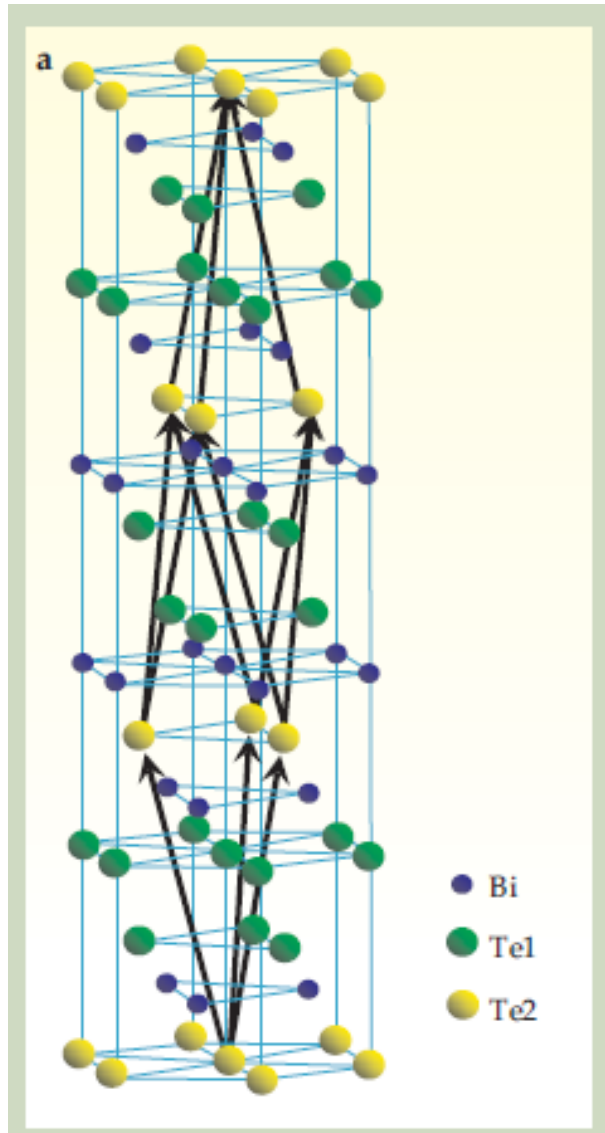


Hasan and Kane, RMP 2010

Qi and Zhang, RMP 2011

Bansil et al., RMP 2016

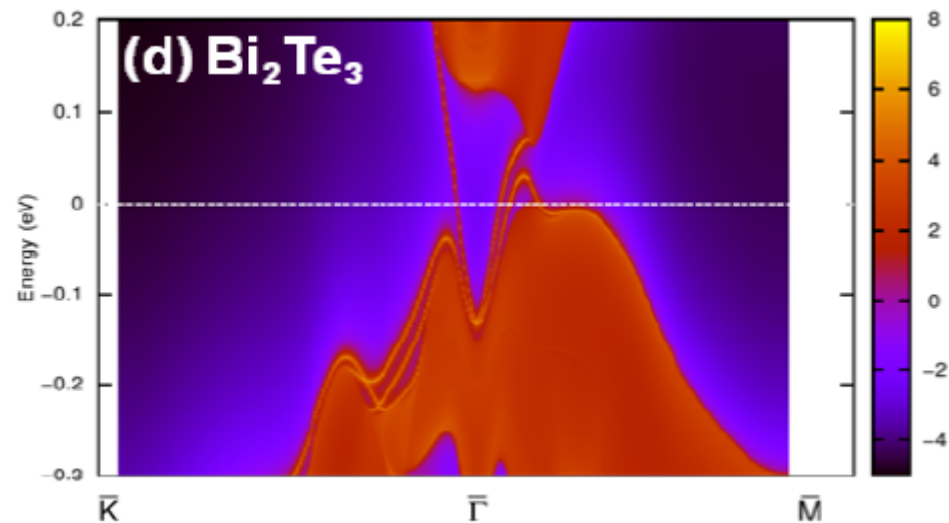
3D Topological Insulators: Bi_2Te_3



$\text{Bi}_{1-x}\text{Sb}_x$, Bi_2Te_3 , Bi_2Se_3 , Sb_2Te_3

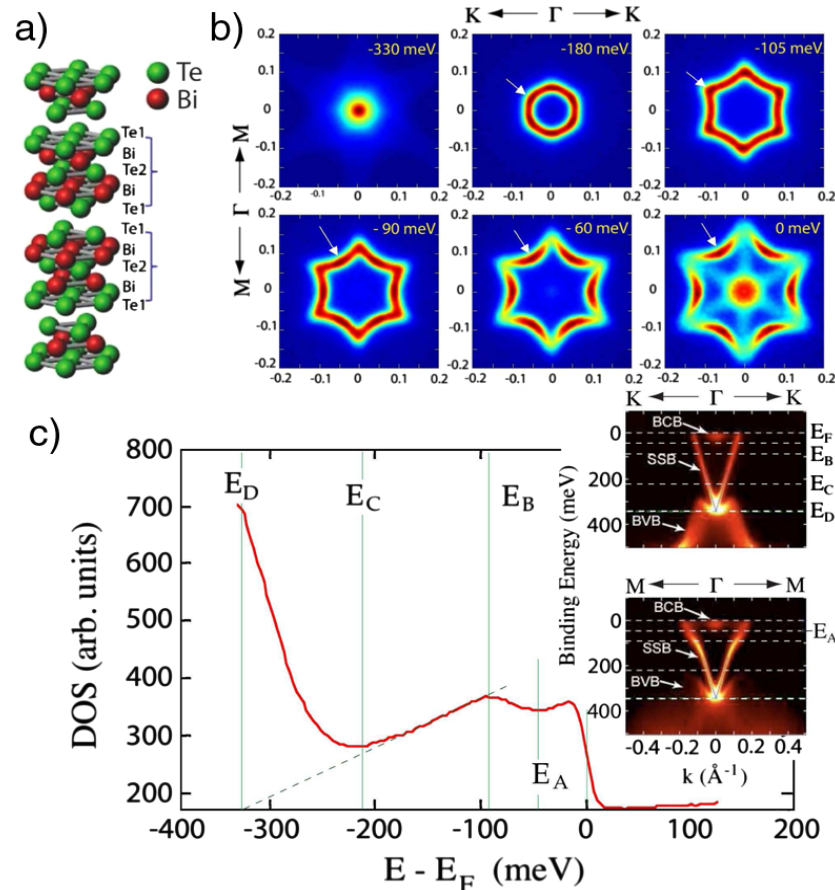
Non trivial topology $\Leftrightarrow$ band inversion driven by strong S-O coupling

→ Single Dirac cone on surface



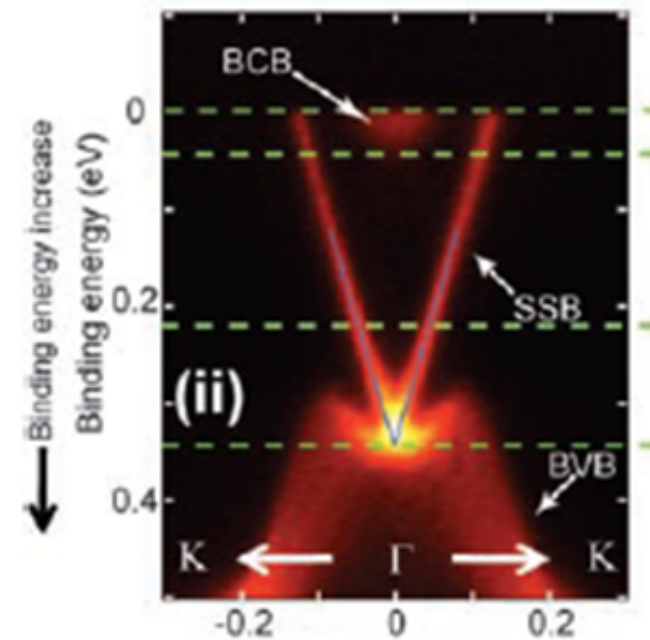
Zhang et al., Nat. Phys. 2009

3D Topological Insulators: Bi_2Te_3



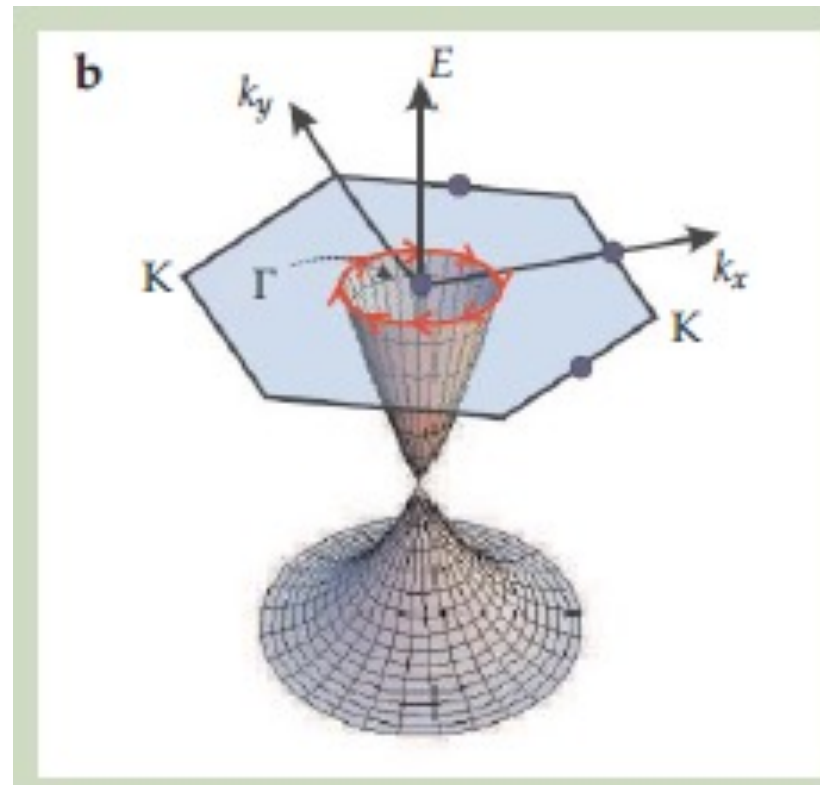
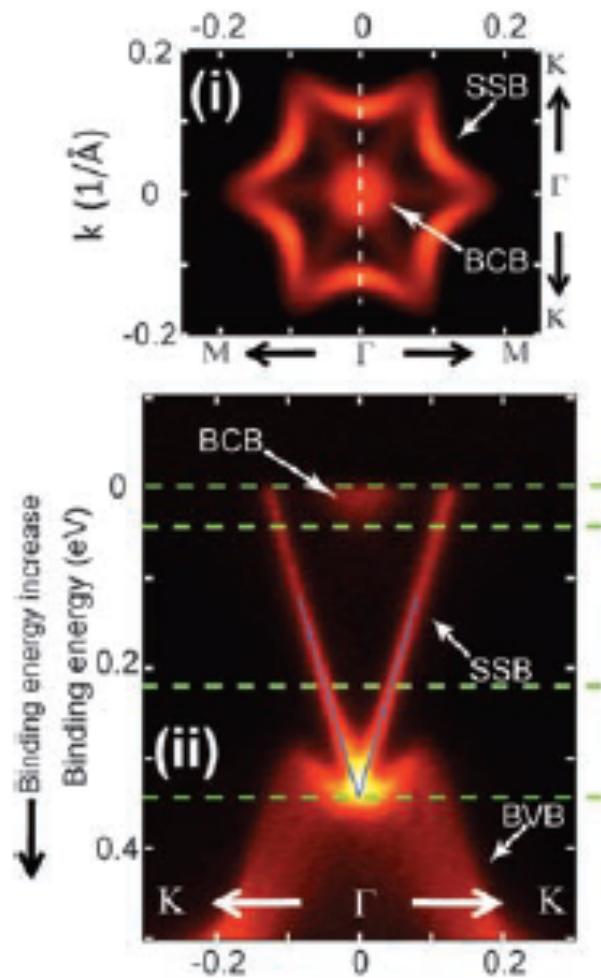
Alpichshev et al., PRL 2010

Bi_2Te_3 : Dirac cone
presents hexagonal warping



3D Topological Insulators $\Leftrightarrow$ ARPES

(Hsieh et al., Nature 2008; Chen et al., Science 2009; ...)



Dirac cone studied by ARPES :
Spin in surface plane, perpendicular to k

Out of equilibrium TI's $\Leftrightarrow$ ultrafast studies

J. Sobota et al., PRL 108, 117403 (2012)

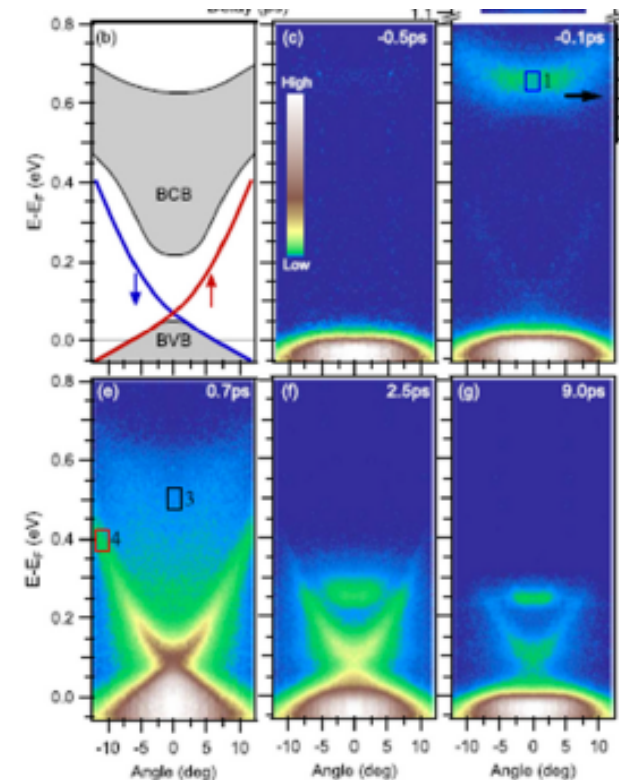
→ out of equilibrium TI's, following first studies in 2012 (Stanford, MIT, Trieste,)

→ Time Resolved ARPES

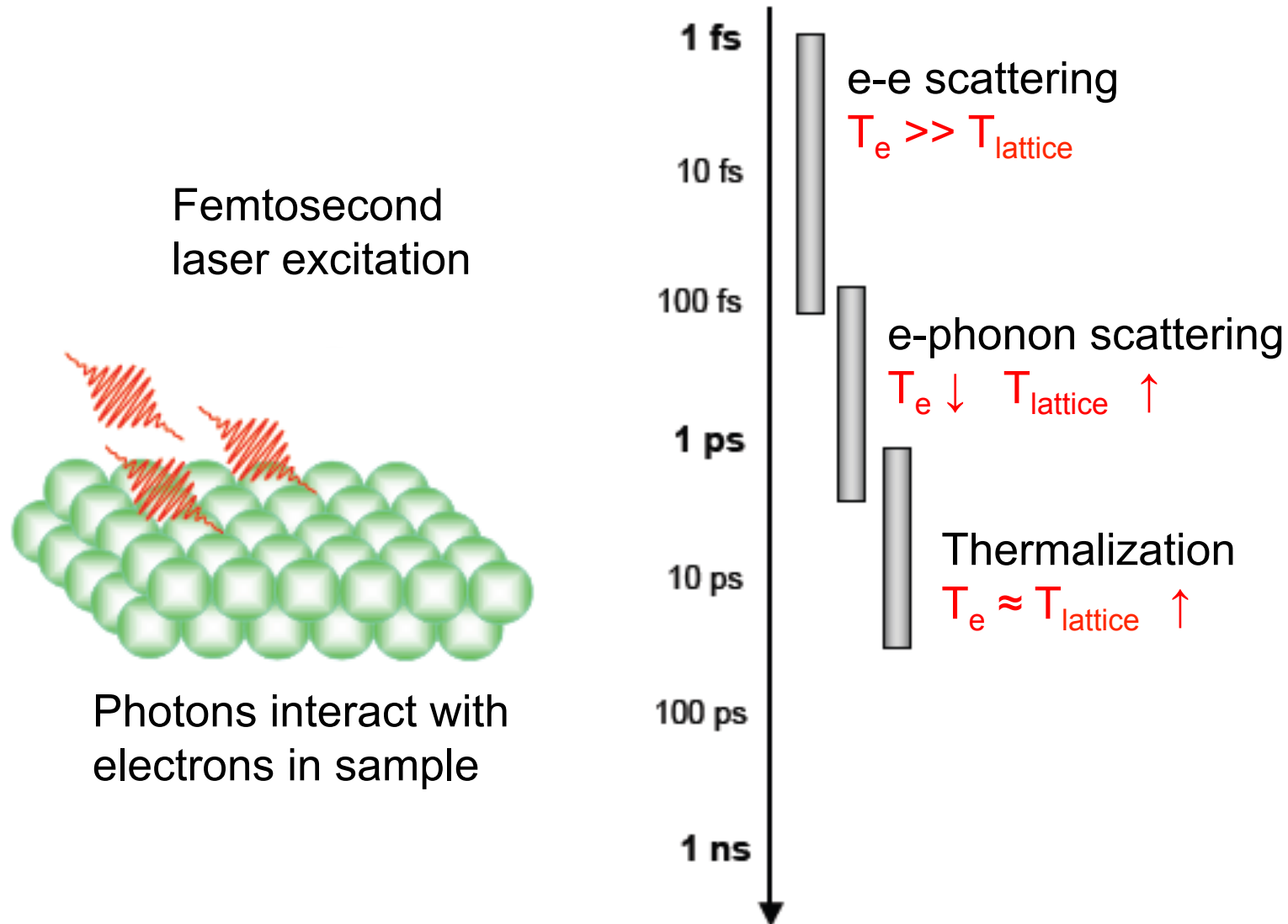
- Info on empty electronic states, interband scattering rates, hot fermion properties?

→ Playground for a 2 dimensional Dirac system (2DDS) in interaction with bulk electronic states

- Thermalization of an out of equilibrium conducting system

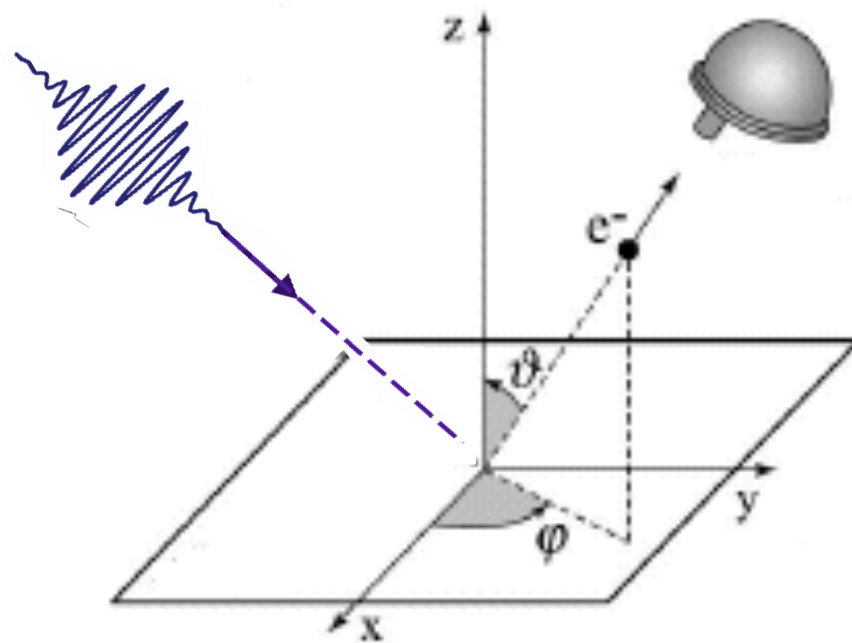


Transient phase $\Leftrightarrow$ e-phonon coupling



ARPES and pump-probe ARPES

- ARPES (Angle Resolved PhotoElectron Spectroscopy)



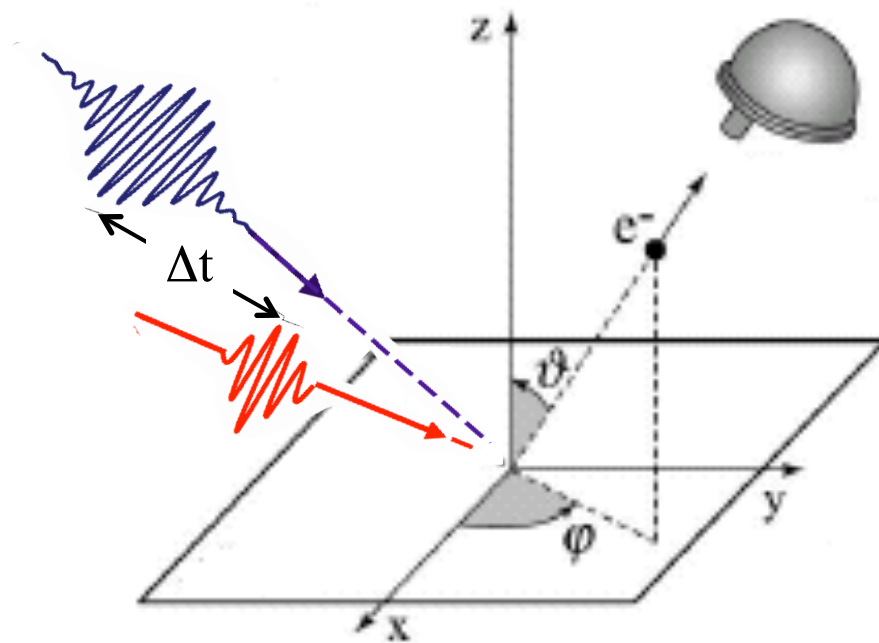
$E(\mathbf{k})$

$$E_B = h\nu - E_K - W$$

$$p_{||} = \hbar k_{||} = \sqrt{2mE_K} \sin \theta ,$$

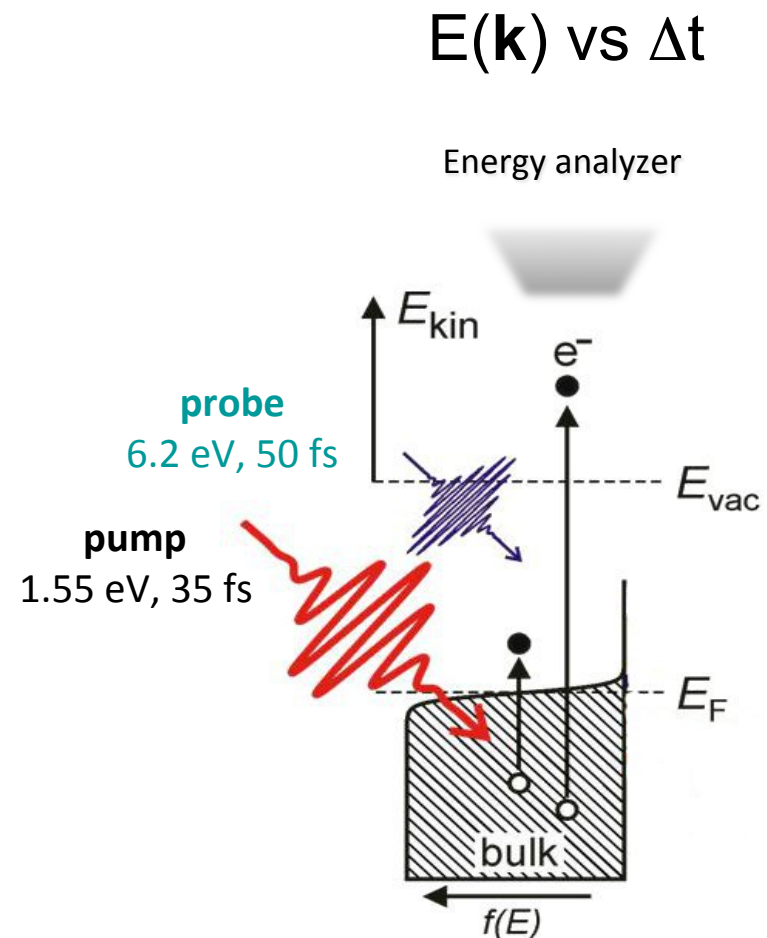
ARPES and pump-probe ARPES

- ARPES (Angle Resolved PhotoElectron Spectroscopy)
- pump-probe ARPES $\Leftrightarrow$ excited states



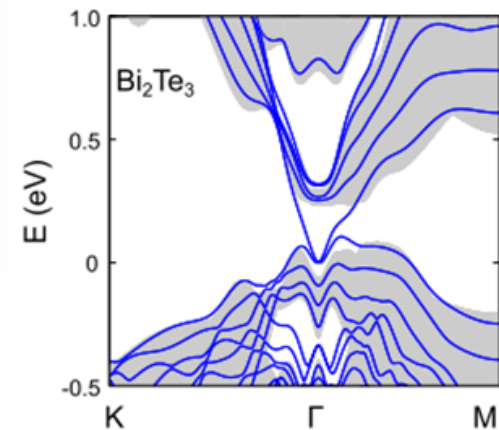
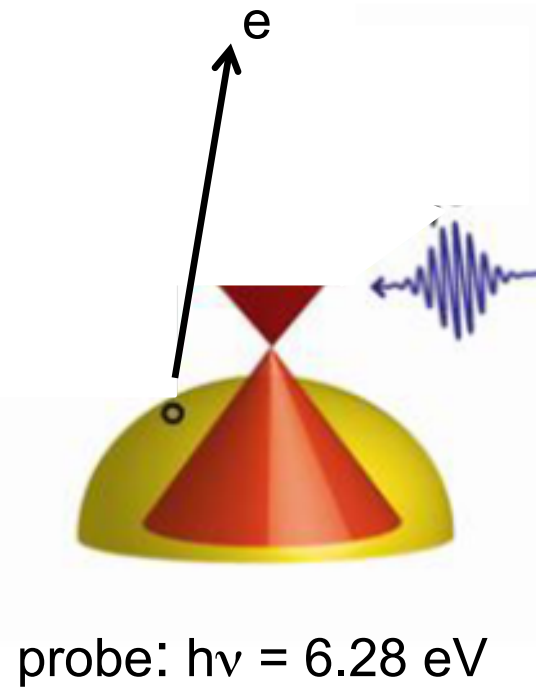
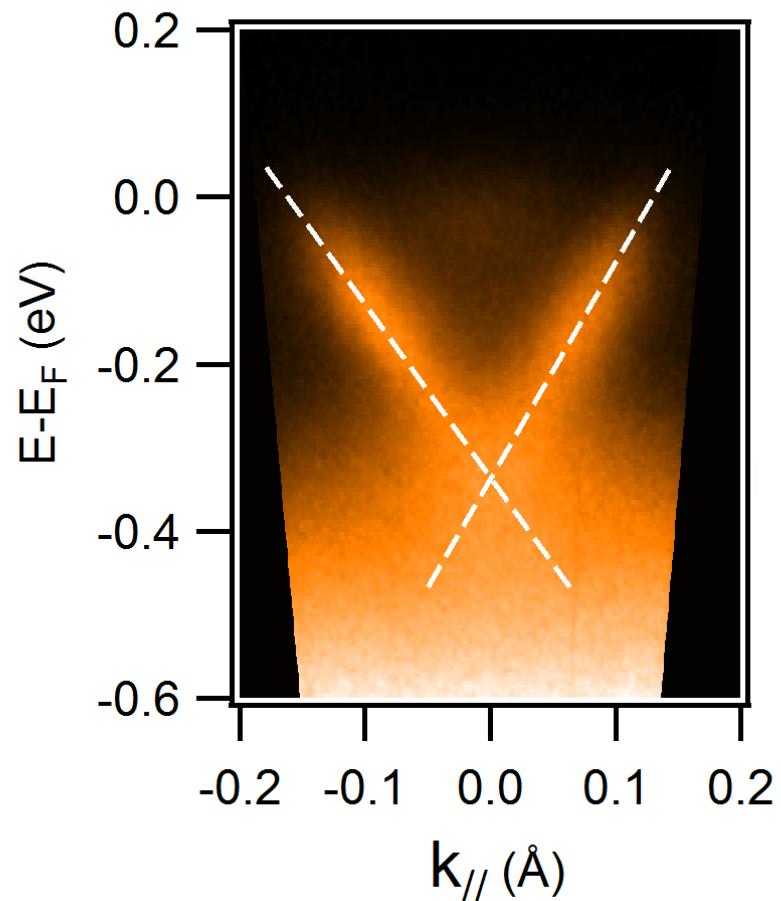
$$E_B = h\nu - E_K - W$$

$$p_{||} = \hbar k_{||} = \sqrt{2mE_K} \sin \theta ,$$



$\text{Bi}_2\text{Te}_3 \Leftrightarrow$ low energy ARPES

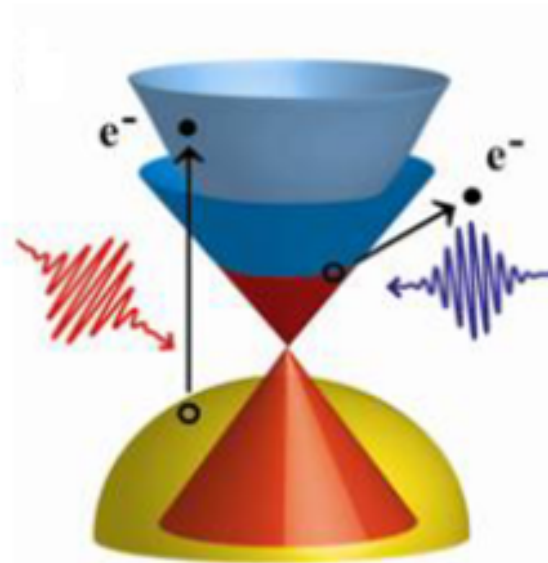
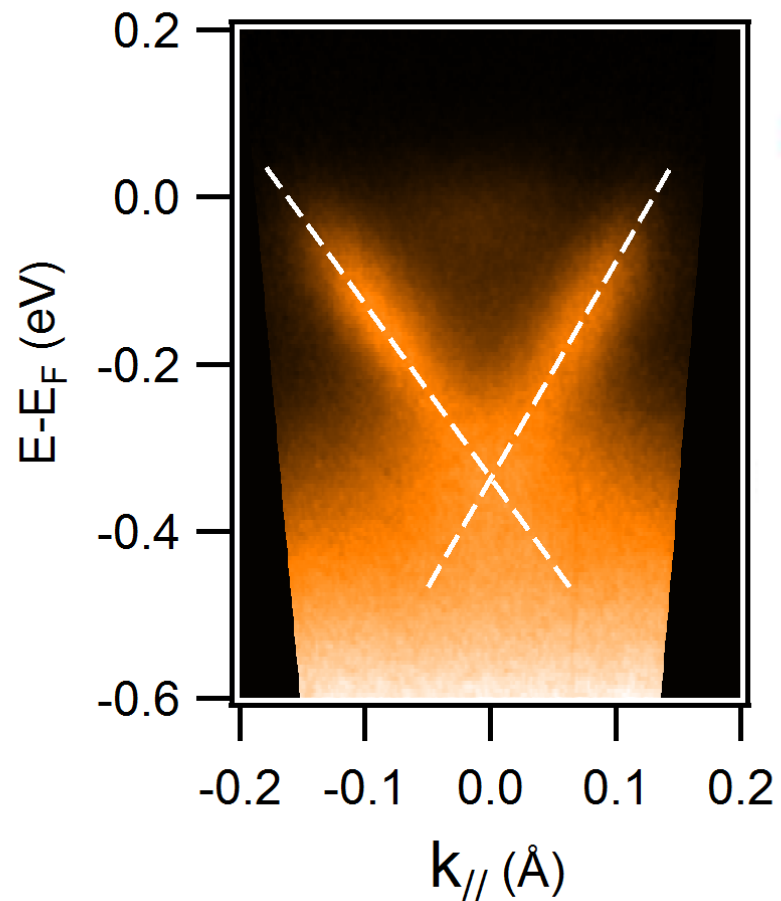
n-type Bi_2Te_3
gap = 0.3 eV



Yazyev and al ,
PRL 105, 266806

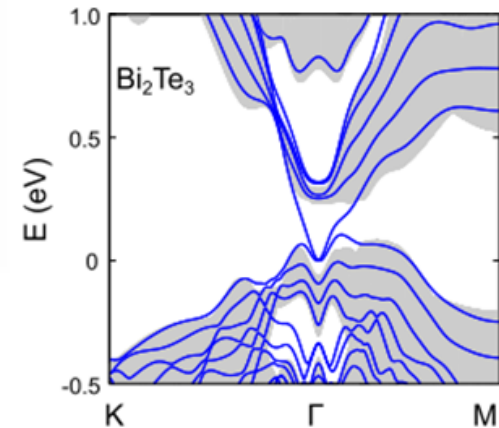
$\text{Bi}_2\text{Te}_3 \rightleftharpoons$ pump-probe ARPES

n-type Bi_2Te_3
gap = 0.3 eV



probe: $h\nu = 6.28$ eV

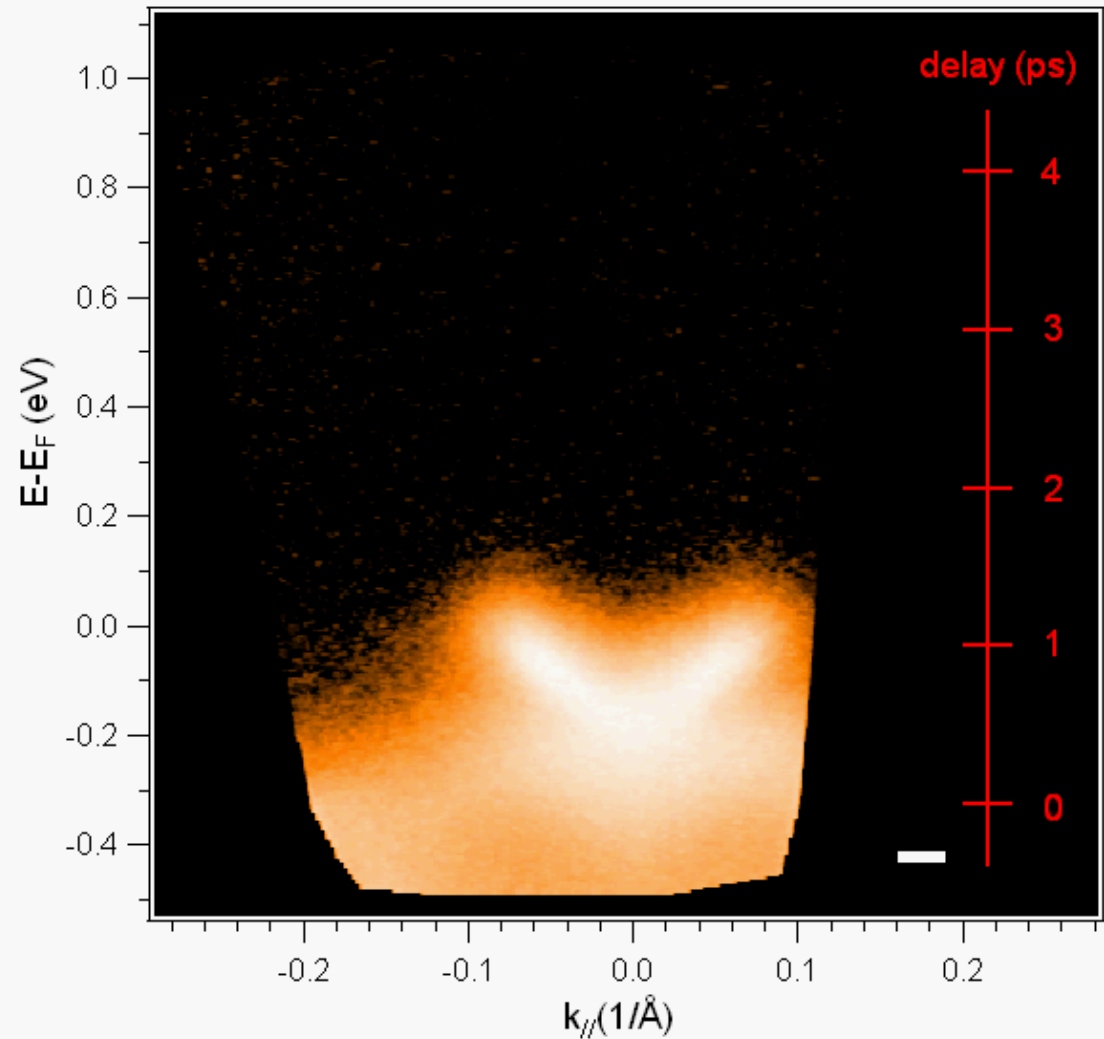
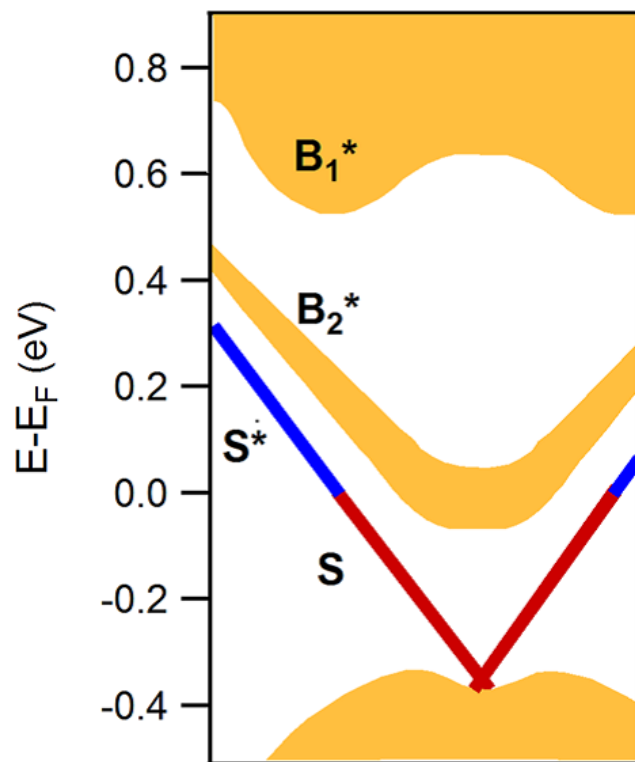
pump: $h\nu = 1.5$ eV



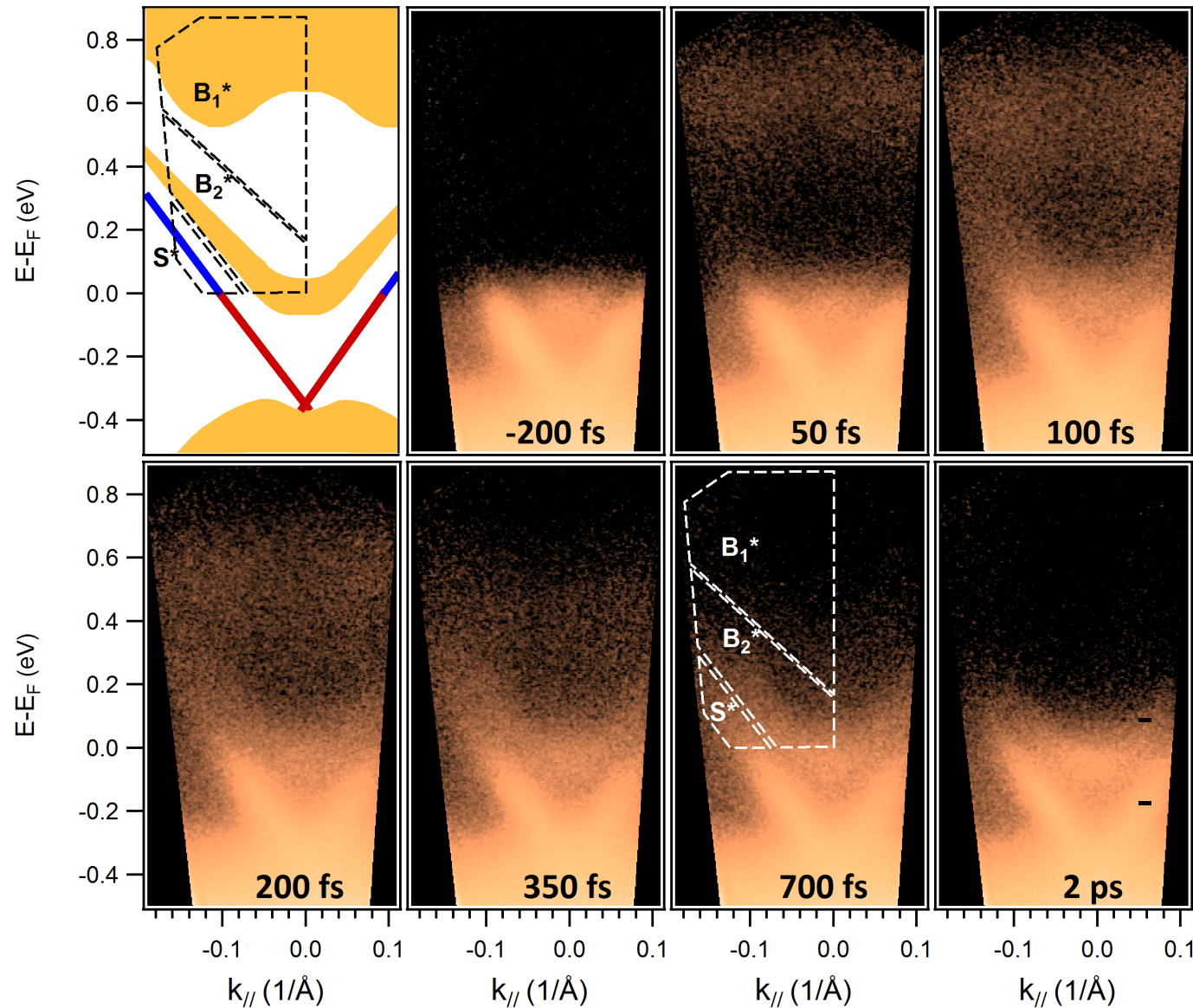
Yazyev and al ,
PRL 105, 266806

Time resolved ARPES on n-Bi₂Te₃

Band structure and
Dirac cone dynamics



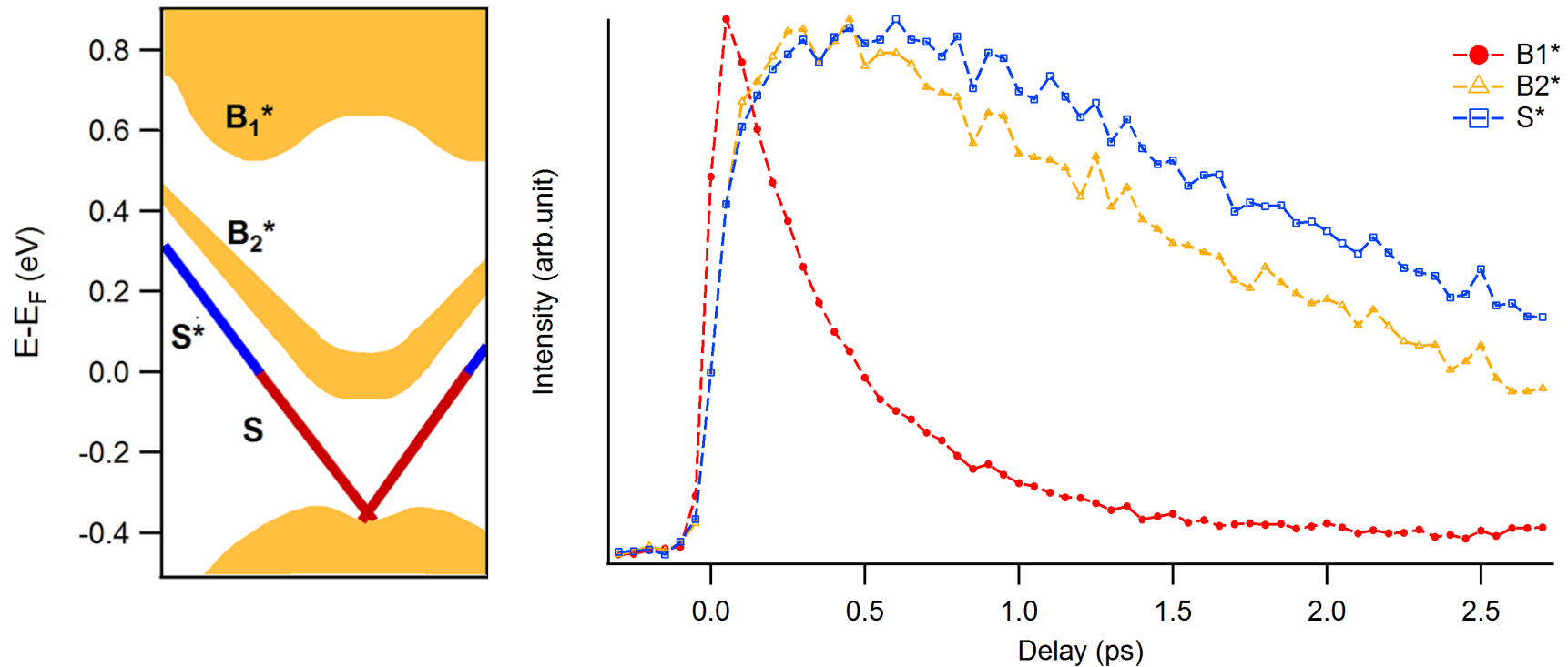
Time resolved ARPES on n-Bi₂Te₃



Ultrafast time
scale for:

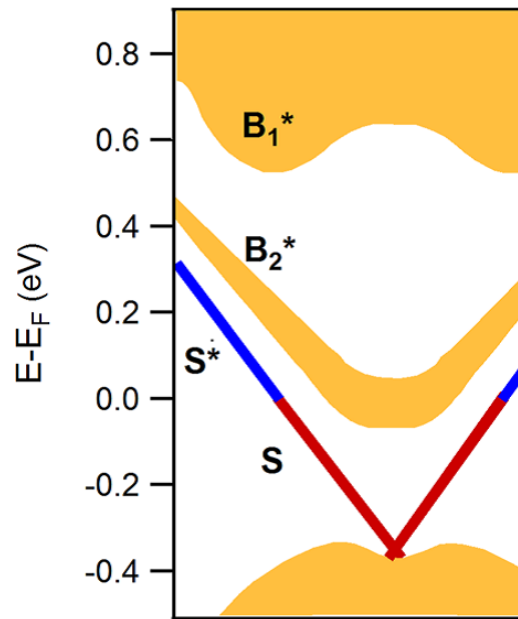
Optical excitation
Interband scattering
Intraband scattering
Hot electron relaxation
-
E-phonon coupling

Transient band populations in n-Bi₂Te₃



- ➔ Excitation VB to B₁^{*}
- ➔ scattering B₁^{*} → S^{*} and B₂^{*}
- ➔ Relaxation of S^{*} slow ⇔ weak e-phonon coupling

Transient band populations



$$\frac{dB_1^*}{dt} = G_1(t) - \frac{B_1^*(t)}{\tau_1}$$

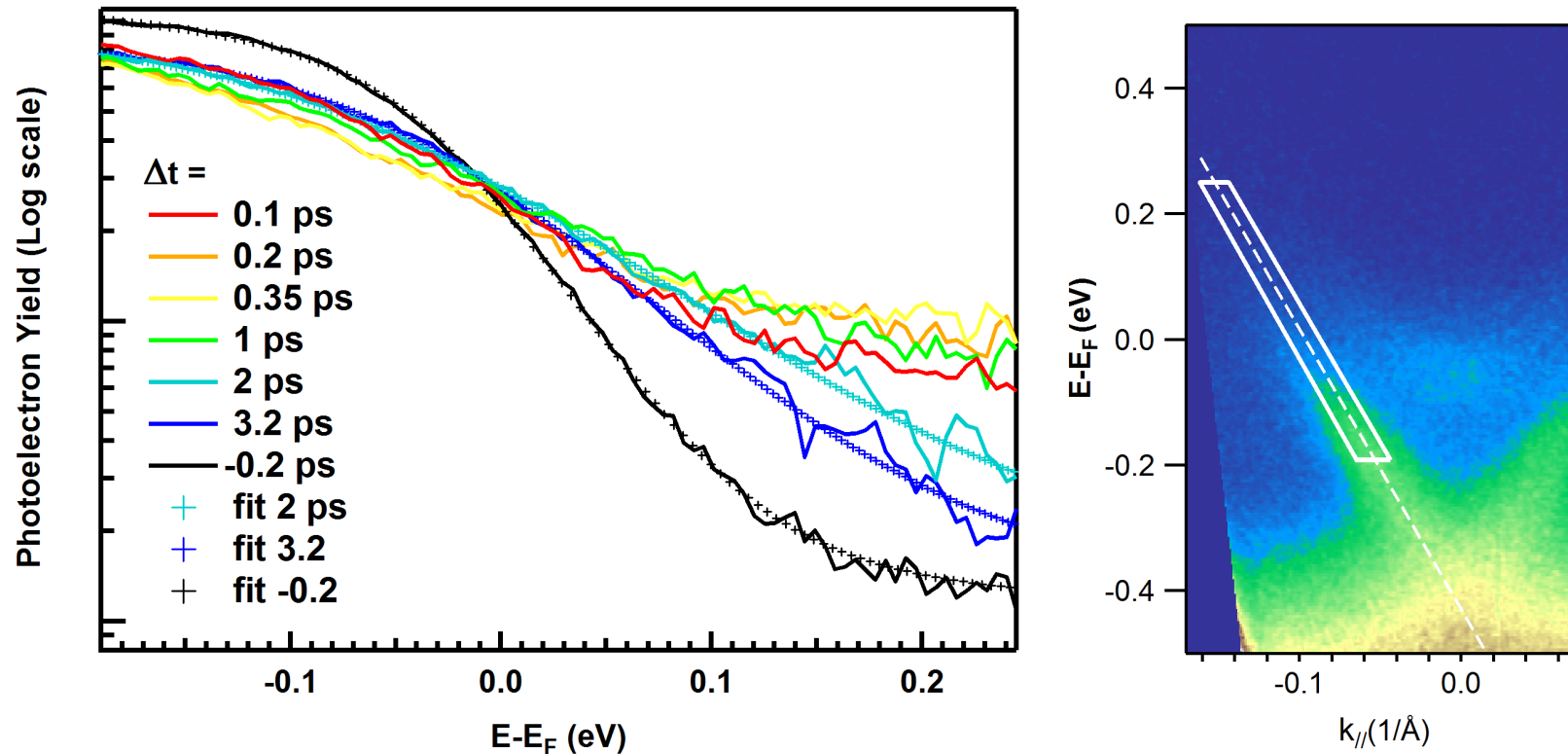
$$\frac{dB_2^*}{dt} = G_2(t) + \alpha \frac{B_1^*(t)}{\tau_1} - \frac{B_2^*(t)}{\tau_2}$$

$$\frac{dS^*}{dt} = G_{S^*}(t) + \beta \frac{B_1^*(t)}{\tau_1} - \frac{S^*(t)}{\tau_{D1}}$$

$$\frac{dS}{dt} = -G_S(t) - \frac{B_{\text{tot}} - B(t)}{\tau_h} + \frac{S_{\text{tot}} - S(t)}{\tau_{D2}}$$

- ➔ Excitation VB to B_1^*
- ➔ scattering $B_1^* \rightarrow S^*$ and B_2^*
- ➔ Relaxation of S^* slow $\Leftrightarrow$ weak e-phonon coupling

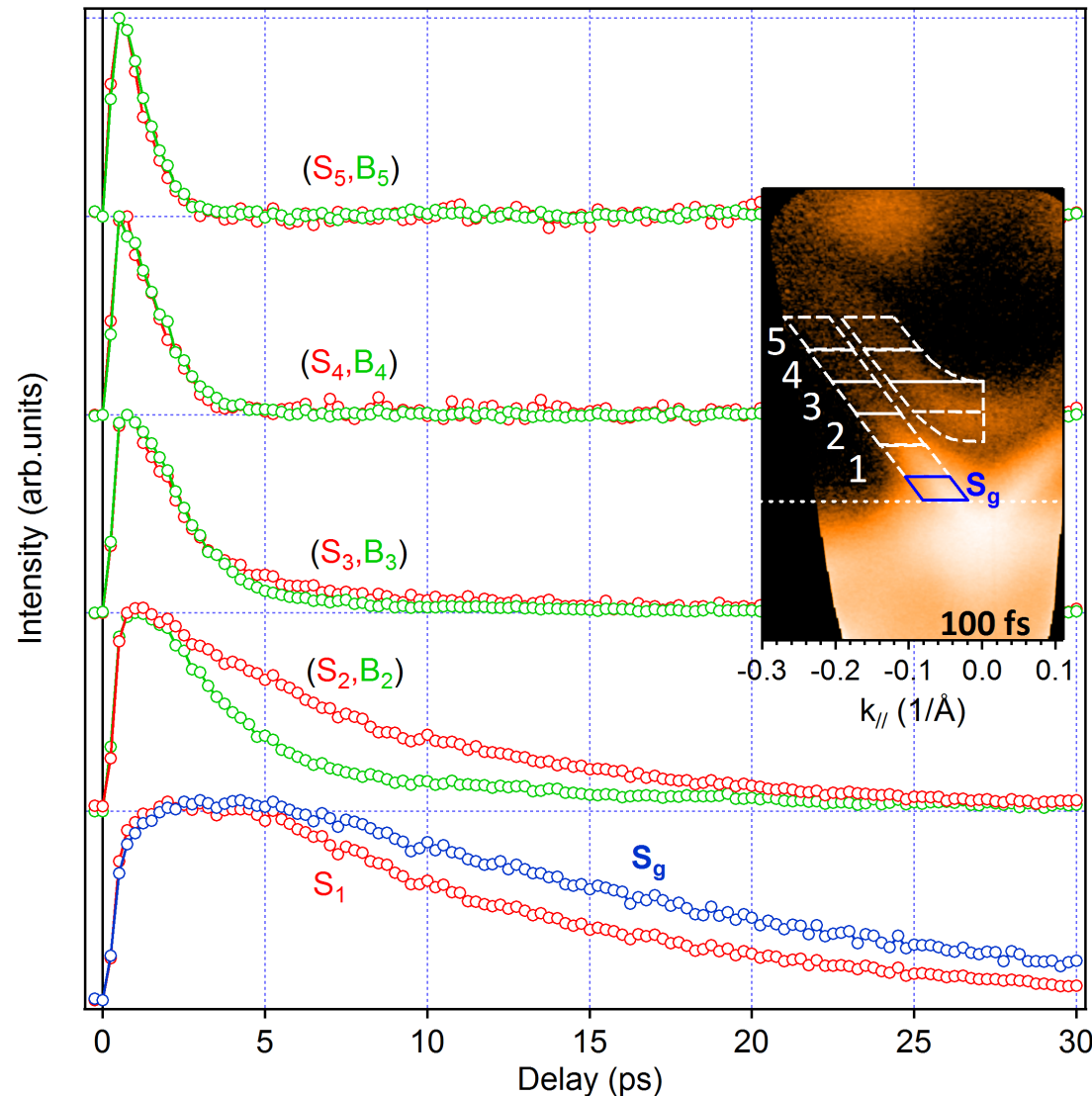
EDC's from transient Dirac cone states



- ➔ Energy Distribution Curves of hot electrons in the Dirac cone
- ➔ electron thermalization: ps scale $\Leftrightarrow$ influenced by interband scattering

Hajlaoui et al., Nano Lett. 12, 3532 (2012)

Dirac cone relaxation in p-Bi₂Te₃



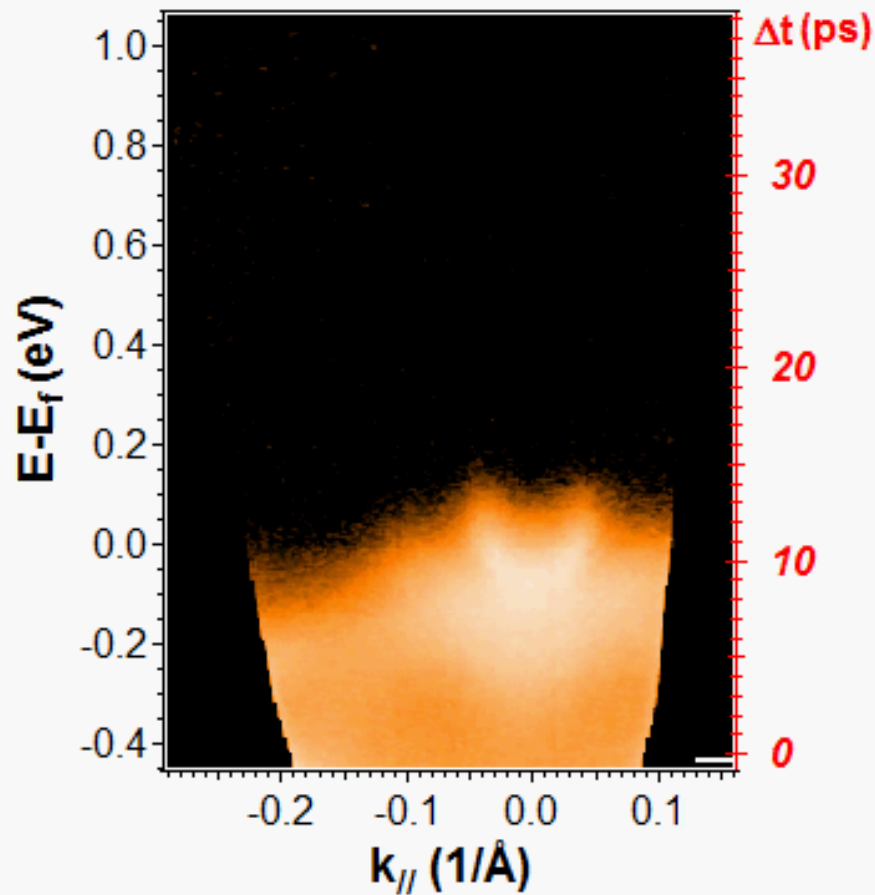
Intrinsic Dirac cone relaxation much slower than bulk recombination

In Bi₂Se₃, exceptionally weak e-ph coupling
(see for instance
Z.-H. Pan et al., PRL 2012
Sobota et al. PRL 2012
Wang et al., PRL 2012)

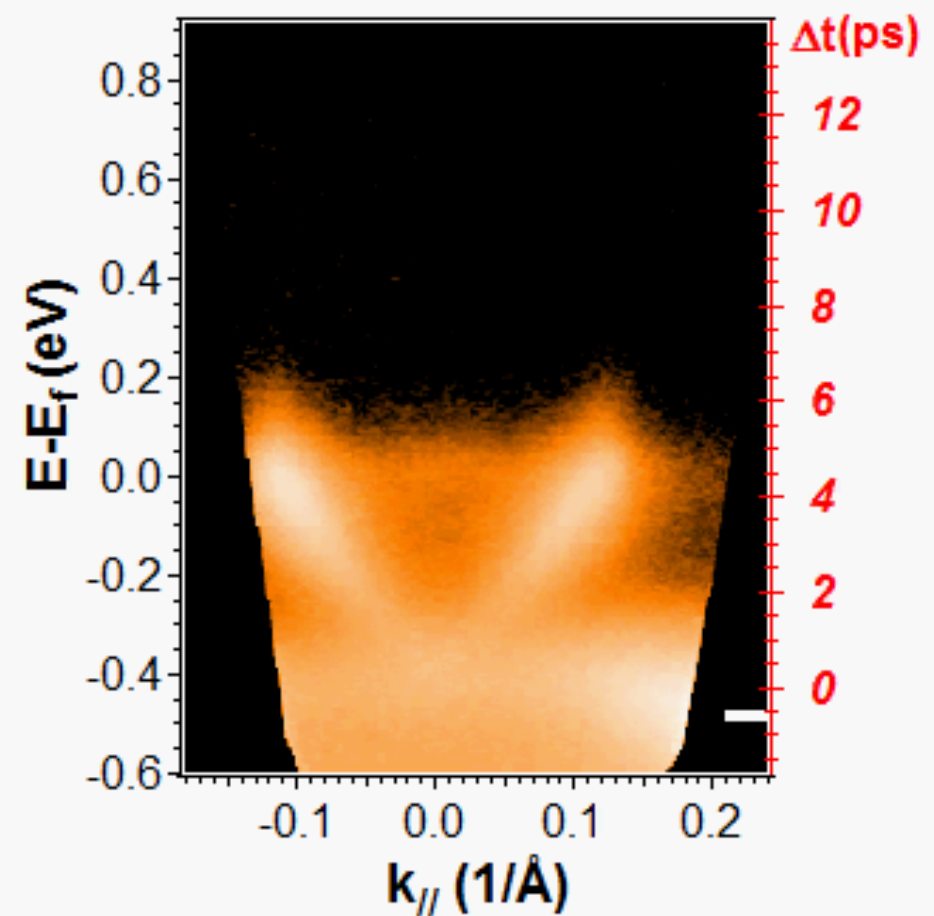
*Hajlaoui et al.,
Nature Comm. 5, 3003 (2014)*

TR-ARPES on p-Bi₂Te₃ n-Bi₂Te₂Se

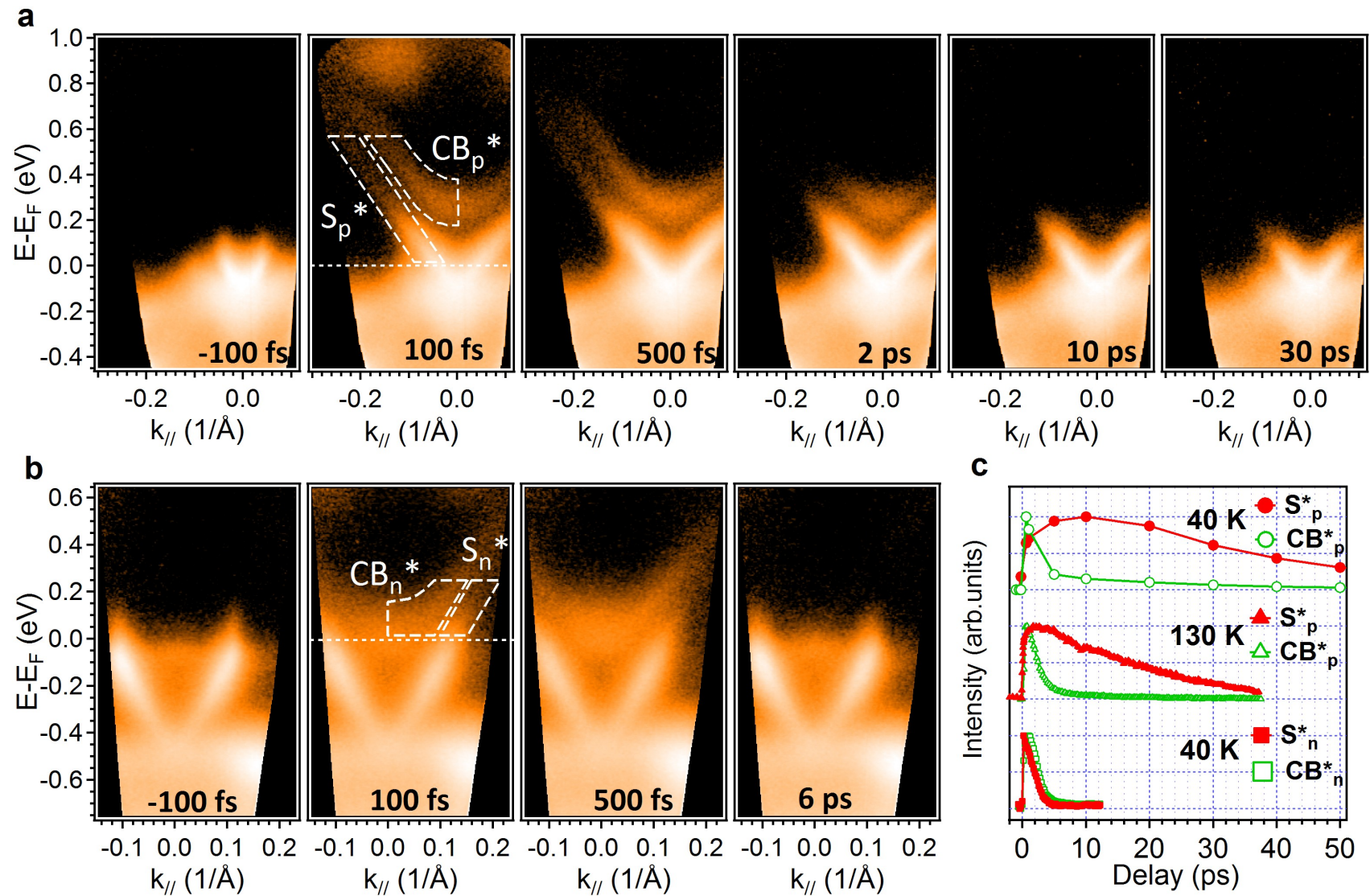
p-Bi₂Te₃



n-Bi₂Te₂Se

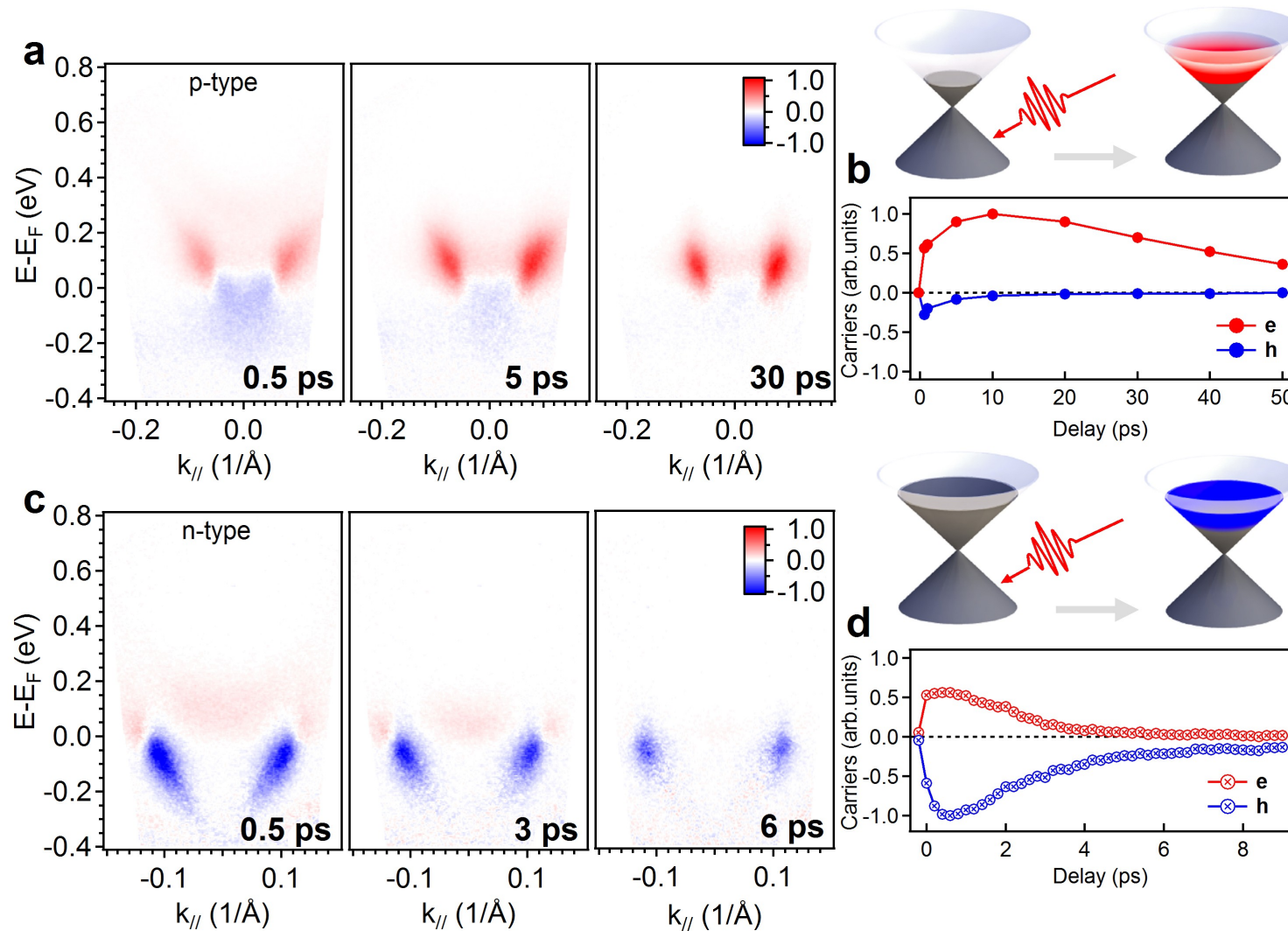


TR-ARPES on p-Bi₂Te₃ n-Bi₂Te₂Se

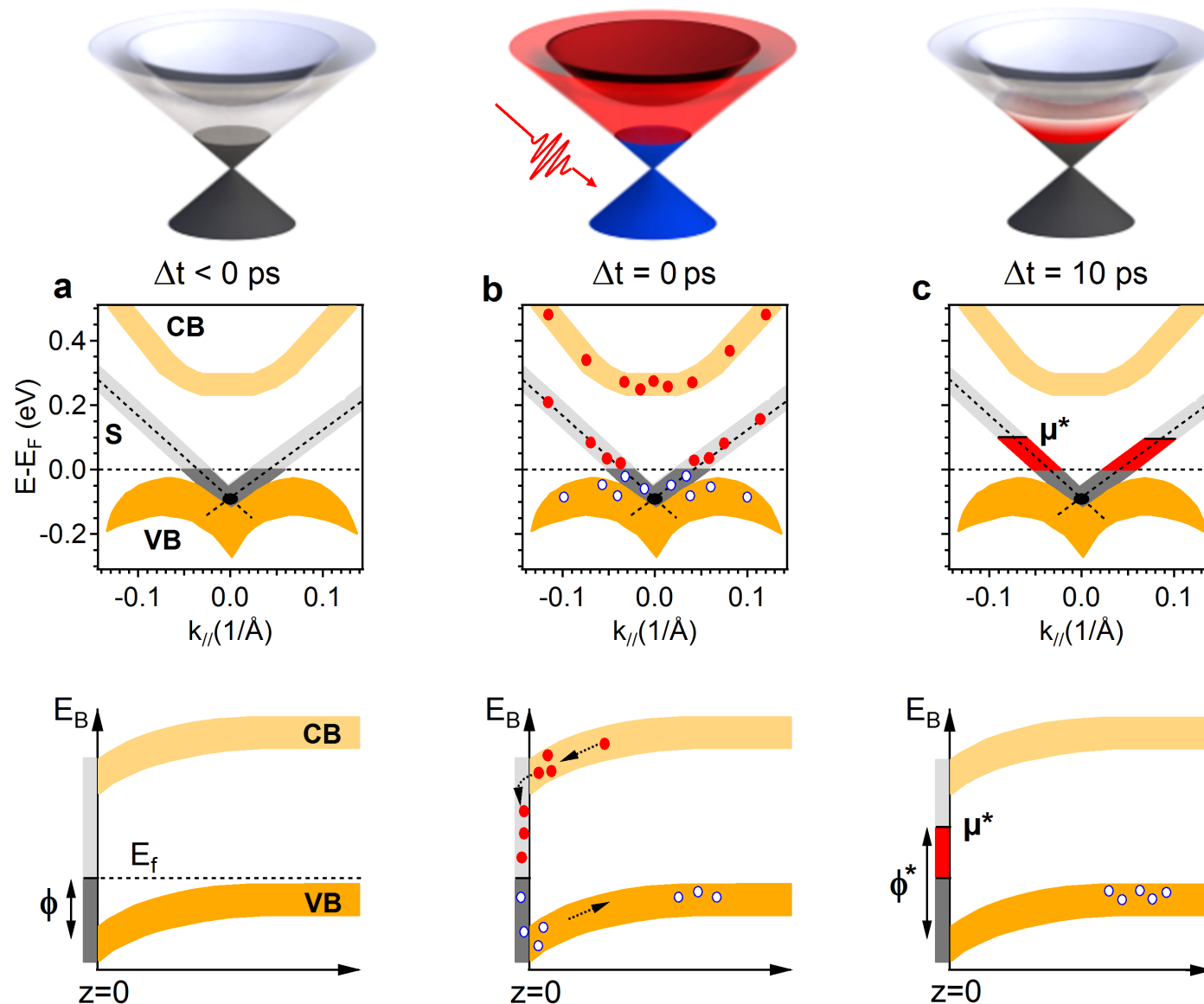


Hajlaoui et al., Nature Commun. 5, 3003 (2014)

Transient e-h asymmetry in Dirac cone

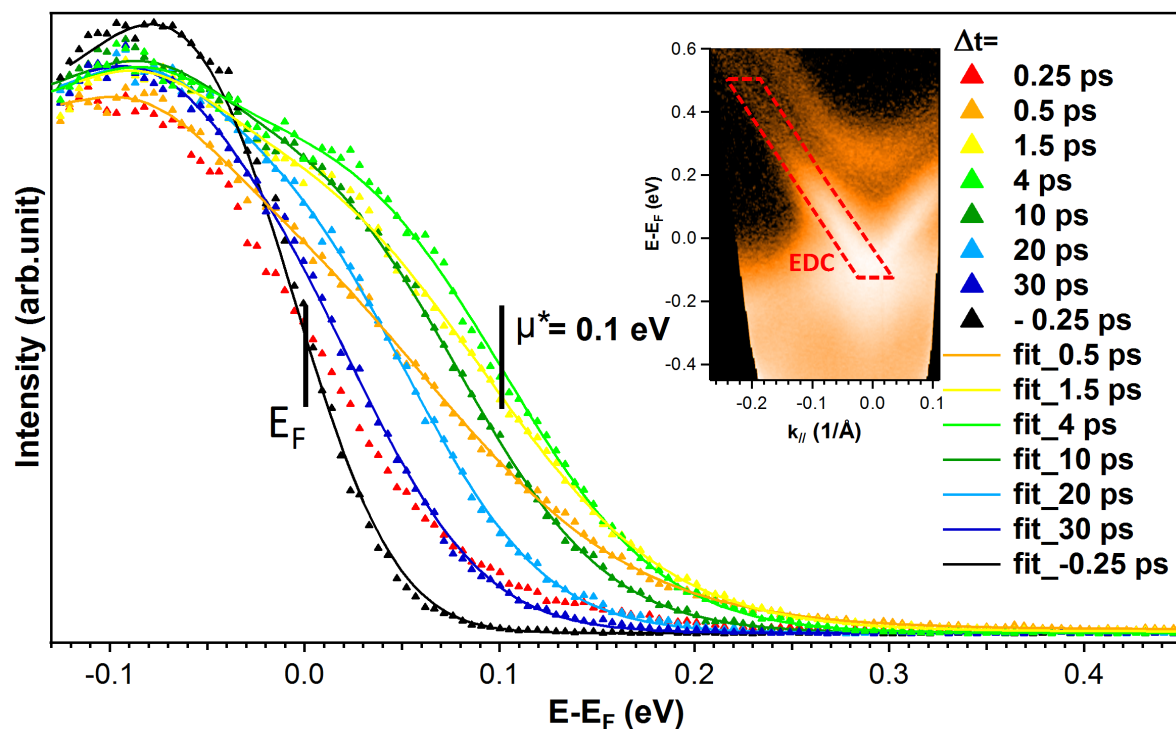


Non equilibrium p-Bi₂Te₃



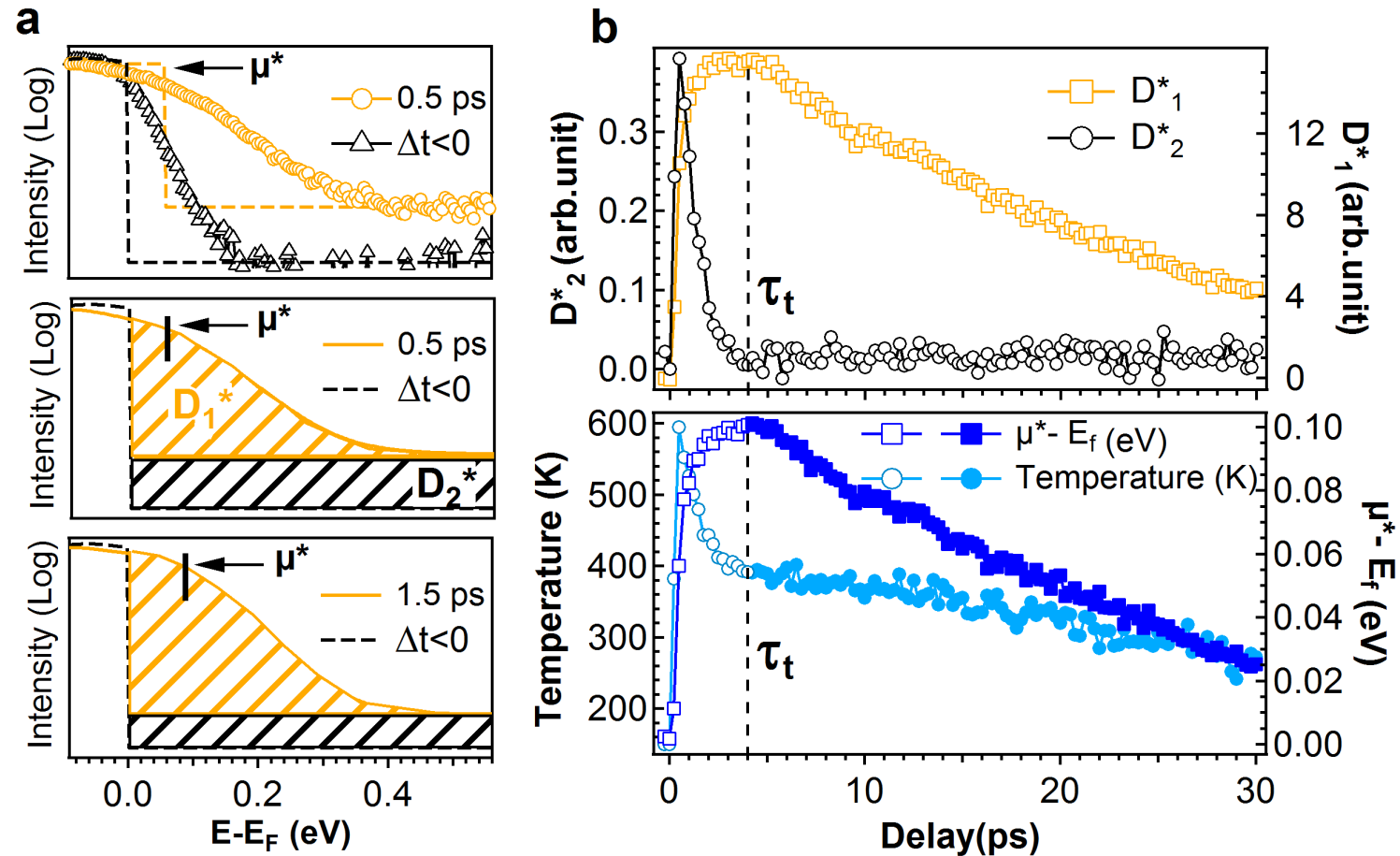
Pre-existing surface band bending helps create a strong e-h transient asymmetry in Dirac cone

Non-equilibrium metallic layer: p-Bi₂Te₃



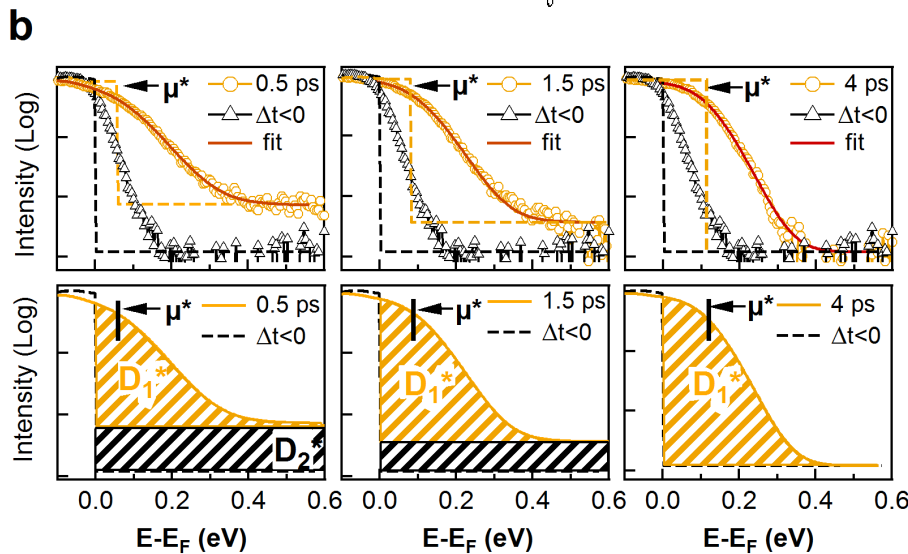
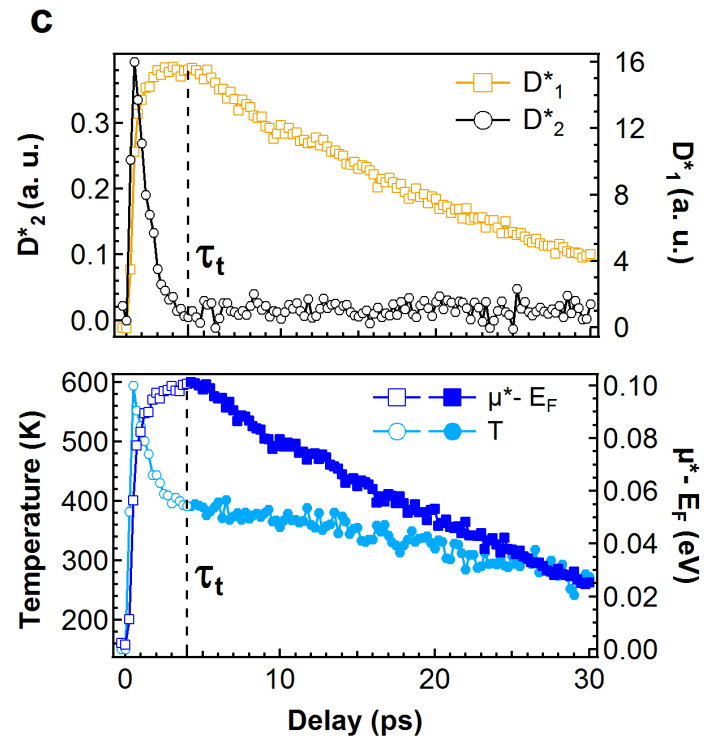
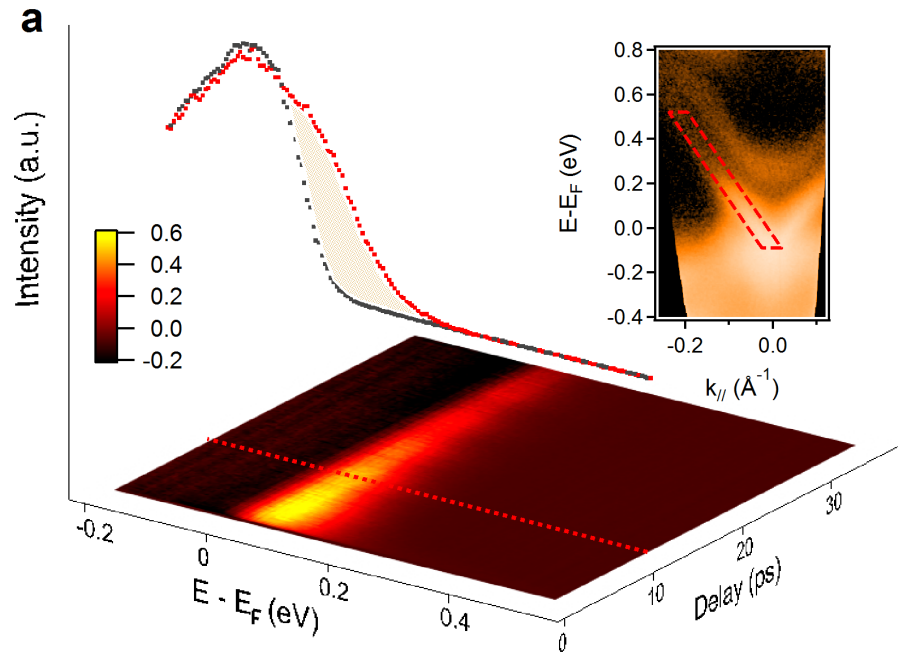
→ Fermi Dirac distribution with $\mu^* > \mu$

Transient temperature, chemical potential in Bi_2Te_3



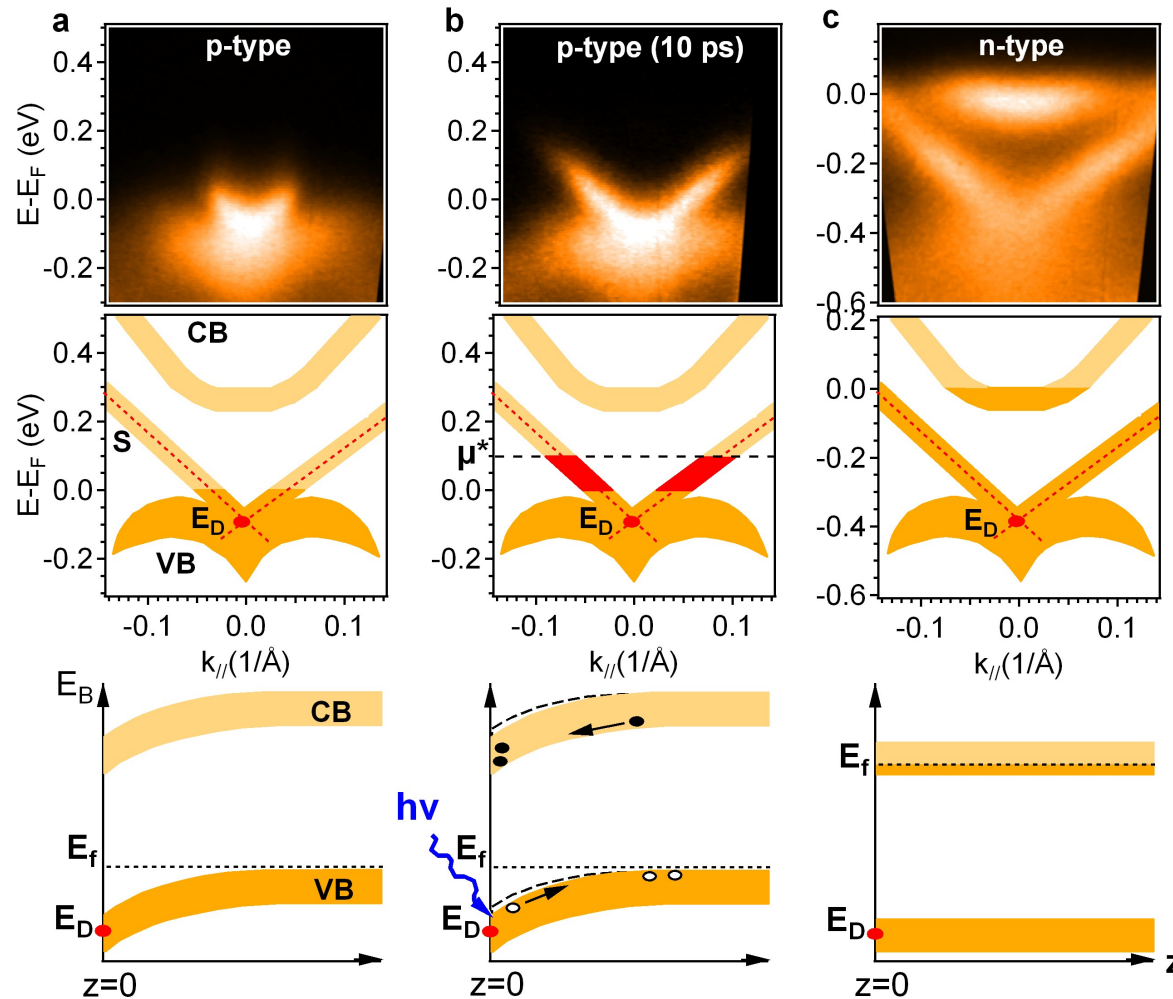
After 4 ps, real Fermi-Dirac distribution

« Hot » Dirac fermions : T^* and μ^*



For $10 \text{ ps} < \Delta t < 50 \text{ ps}$,
 $\mu^* > \mu$ in surface metallic layer,
 while bulk bands are at equilibrium

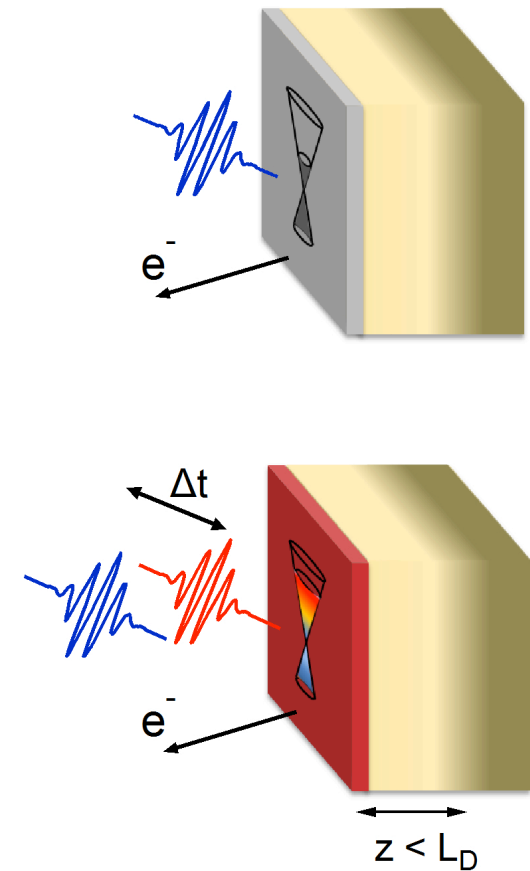
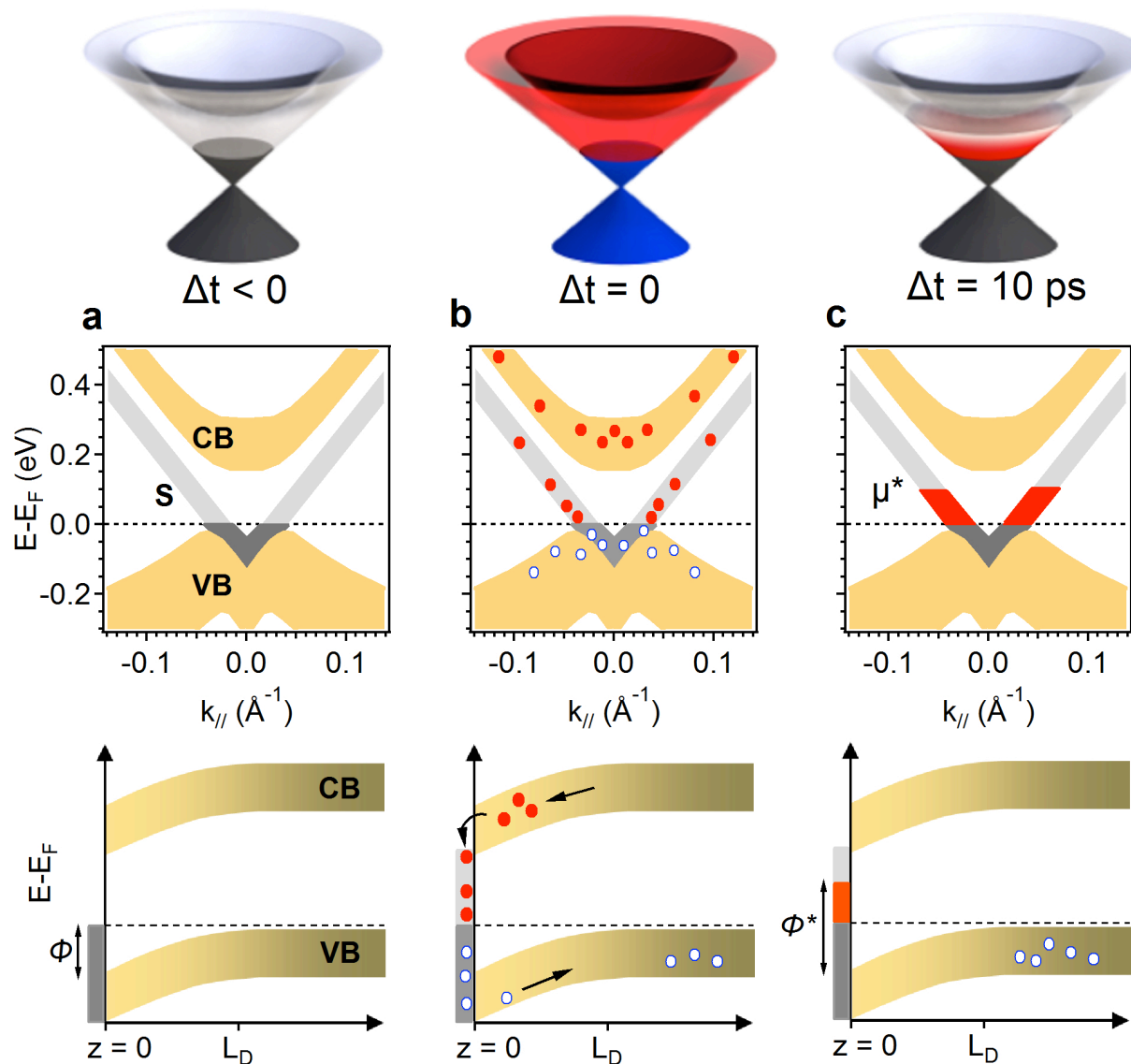
« Transient Topological Insulator »



For $\Delta t > 10$ ps
photoexcited p-
type looks like an
n-type with no
electrons in bulk
conduction band

→ « real TI* »,
Insulating bulk vs
conducting surface
in photoexcited
state

Transient tuning of a nm-scale Schottky barrier



$\phi^* > \phi$ due to strongly out of equilibrium 2DDS

Conclusion and perspectives

- ➔ Dirac cone dynamics in Bi_2Te_3 : direct observation of inter- and intra-band scattering, electron-phonon coupling, hot electron relaxation
- ➔ Long time for Dirac cone relaxation, weak electron-phonon coupling
- ➔ Possibility of creating a strong e-h asymmetry in Dirac cone
- ➔ Strongly out of equilibrium ($\mu^*=0.1$ eV), long lived (50 ps) excited conducting system, impossible to obtain in a conventional metal
- ➔ Photoinduced tuning of a nanoscale Schottky barrier
- ➔ SEE POSTER Lama Khalil (Monday afternoon): continuing these studies on materials with reduced bulk conductivity

Thanks to:



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